

RAD-TOLERANT CLASS V, HIGH-SPEED PWM CONTROLLER

Check for Samples: UC1825-SP

FEATURES

- QML-V Qualified, SMD 5962-87681
- Rad-Tolerant: 30 kRad (Si) TID (1)
- Compatible With Voltage- or Current-Mode Topologies
- Practical Operation Switching Frequencies to 1 MHz
- 50-ns Propagation Delay-to-Output
- High-Current Dual Totem Pole Outputs (1.5 A Peak)
- Wide Bandwidth Error Amplifier
- Fully Latched Logic With Double-Pulse Suppression
- Pulse-by-Pulse Current Limiting
- Soft Start/Maximum Duty-Cycle Control
- Undervoltage Lockout With Hysteresis
- Low Start-Up Current (1.1 mA)
- Radiation tolerance is a typical value based upon initial device qualification with dose rate = 10 mrad/sec. Radiation Lot Acceptance Testing is available - contact factory for details.

DESCRIPTION

The UC1825 PWM control device is optimized for high-frequency switched mode power supply applications. Particular care was given to minimizing propagation delays through the comparators and logic circuitry while maximizing bandwidth and slew rate of the error amplifier. This controller is designed for use in either current-mode or voltage mode systems with the capability for input voltage feed-forward.

Protection circuitry includes a current limit comparator with a 1-V threshold, a TTL compatible shutdown port, and a soft start pin which will double as a maximum duty-cycle clamp. The logic is fully latched to provide jitter-free operation and prohibit multiple pulses at an output. An undervoltage lockout section with 800 mV of hysteresis assures low start up current. During undervoltage lockout, the outputs are high impedance.

This device features totem pole outputs designed to source and sink high peak currents from capacitive loads, such as the gate of a power MOSFET. The on state is designed as a high level.

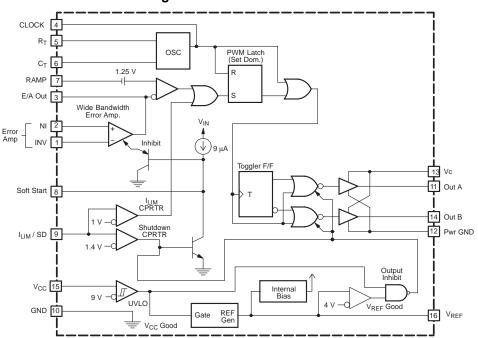


Figure 1. BLOCK DIAGRAM



Please be aware that an important notice concerning availability, standard warranty, and use in critical applications of Texas Instruments semiconductor products and disclaimers thereto appears at the end of this data sheet.

VDG-92032-2





This integrated circuit can be damaged by ESD. Texas Instruments recommends that all integrated circuits be handled with appropriate precautions. Failure to observe proper handling and installation procedures can cause damage.

ESD damage can range from subtle performance degradation to complete device failure. Precision integrated circuits may be more susceptible to damage because very small parametric changes could cause the device not to meet its published specifications.

Table 1. ORDERING INFORMATION⁽¹⁾

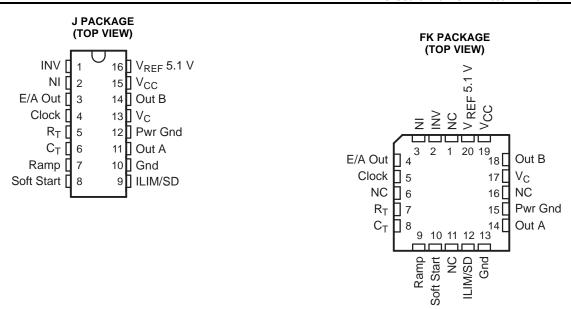
T _A	PACKAGE ⁽²⁾	ORDERABLE PART NUMBER	TOP-SIDE MARKING
–55°C to 125°C	CDIP – J	5962-8768104VEA	UC1825J-SP
-55 0 10 125 0	LCCC – FK	5962-8768104V2A	UC1825FK-SP

⁽¹⁾ For the most current package and ordering information, see the Package Option Addendum at the end of this document, or see the TI web site at www.ti.com.

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⁽²⁾ Package drawings, thermal data, and symbolization are available at www.ti.com/packaging.





TERMINAL FUNCTIONS

NARAE		NO.	1/0	DECCRIPTION			
NAME	J	FK	I/O	DESCRIPTION			
Clock	4	5	0	Output of the internal oscillator			
C _T	6	8	I	Timing capacitor connection pin for oscillator frequency programming. The timing capacitor should be connected to the device ground using minimal trace length.			
E/A Out	3	4	0	Output of the error amplifier for compensation			
Gnd	10	13	-	Analog ground return pin			
ILIM/SD	9	12	I	Input to the current limit comparator and the shutdown comparator			
INV	1	2	I	Inverting input to the error amplifier			
NC		1, 6, 11, 16	-	No connection			
NI	2	3	1	Non-inverting input to the error amplifier			
Out A	11	14	0	High-current totem pole output A of the on-chip drive stage			
Out B	14	18	0	High-current totem pole output B of the on-chip drive stage			
Pwr Gnd	12	15	-	Ground return pin for the output driver stage			
Ramp	7	9	ı	Non-inverting input to the PWM comparator with 1.25-V internal input offset. In voltage mode operation this serves as the input voltage feed-forward function by using the CT ramp. In peak current mode operation, this serves as the slope compensation input.			
R _T	5	7	1	Timing resistor connection pin for oscillator frequency programming			
Soft Start	8	10	I	Soft-start input pin which also doubles as the maximum duty cycle clamp			
V _C	13	17	-	Power supply pin for the output stage. This pin should be bypassed with a 0.1-µF monolithic ceramic low ESL capacitor with minimal trace lengths.			
V _{CC}	15	19	-	Power supply pin for the device. This pin should be bypassed with a 0.1-µF monolithic ceramic low ESL capacitor with minimal trace lengths.			
V _{REF} 5.1 V	16	20	0	5.1-V reference. For stability, the reference should be bypassed with a 0.1-µF monolithic ceramic low ESL capacitor and minimal trace length to the ground plane.			



ABSOLUTE MAXIMUM RATINGS(1)

			UNIT	
Supply voltage	V _C , V _{CC}	30	V	
Output surrent source or sink Out A Out B	DC	0.5	_	
Output current, source or sink, Out A, Out B	Pulse (0.5 μs)	2.0	Α	
Analog Spring	INV, NI, Ramp	-0.3 to 7		
Analog inputs	Soft Start, ILIM/SD	-0.3 to 6	V	
Clock output current	Clock	-5		
Error amplifier output current	E/A Out	5	4	
Soft-start sink current	Soft Start	20	mA	
Oscillator charging current	R _T	-5		
Power dissipation		1	W	
Storage temperature range		-65 to 150	°C	
Lead temperature (soldering, 10 seconds)		300	30	

⁽¹⁾ All voltages are with respect to GND; all currents are positive into, negative out of part; pin numbers refer to DIL-16 package.

RECOMMENDED OPERATING CONDITIONS

over operating free-air temperature range ($T_A = T_J = -55^{\circ}\text{C}$ to 125°C), unless otherwise noted.

		MIN	MAX	UNIT
V_{CC}	Supply voltage	10	30	V
	Sink/source output current (continuous or time average)	0	100	mA
	Reference load current	0	10	mA

THERMAL RATINGS TABLE

PACKAGE	θ _{JA} (°C/W)	θ _{JC} (°C/W)
DIL-16 (J)	80–120	28 ⁽¹⁾
LCC-20 (FK)	70–80	20 ⁽¹⁾

⁽¹⁾ θ_{JC} data values stated were derived from MIL-STD-1835B. MIL-STD-1835B states that the baseline values shown are worst case (mean + 2s) for a 60 x 60 mil microcircit device silicon die and applicable for devices with die sizes up to 14400 square mils. For device die sizes greater than 14400 square mils use the following values; dual-in-line, 11°C/W; flat pack 10°C/W; pin grid array, 10°C/W.

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ELECTRICAL CHARACTERISTICS

Unless otherwise stated, these specifications apply for $R_T = 3.65 \text{ k}\Omega$, $C_T = 1 \text{ nF}$, $V_{CC} = 15 \text{ V}$, $-55^{\circ}\text{C} < T_A < 125^{\circ}\text{C}$, $T_A = T_J$

PARAMETERS	TEST CONDITIONS	MIN	TYP	MAX	UNIT
REFERENCE		-			
Output voltage	T _J = 25°C, I _O = 1 mA	5.05	5.10	5.15	V
Line regulation	10 V < V _{CC} < 30 V		2	20	mV
Load regulation	1 mA < I _O < 10 mA		5	20	mV
Total output variation	Line, load, temperature	5.0		5.2	V
Output noise voltage	10 Hz < f < 10 kHz		50		μV
Short-circuit current	V _{REF} = 0 V	-15	-50	-100	mA
OSCILLATOR SECTION					
Initial accuracy	T _J = 25°C	360	400	440	kHz
Voltage stability	10 V < V _{CC} < 30 V		0.2%	2%	
Temperature stability	$T_{MIN} < T_A < T_{MAX}$		5%	16%	
Total variation	Line, Temperature	340		460	kHz
Clock out high		3.9	4.5		V
Clock out low			2.3	2.9	V
Ramp peak ⁽¹⁾		2.6	2.8	3.0	V
Ramp valley ⁽¹⁾		0.7	1.0	1.25	V
Ramp valley to peak ⁽¹⁾		1.6	1.8	2.1	V
ERROR AMPLIFIER					
Input offset voltage				10	mV
Input bias current			0.6	3	μΑ
Input offset current			0.1	1	μΑ
Open-loop gain	1 V < V _O < 4 V	60	95		dB
CMRR	1.5 V < V _{CM} < 5.5 V	75	95		dB
PSRR	10 V < V _{CC} < 30 V	85	110		dB
Output sink current	V _{E/AOut} = 1 V	1	2.5		mA
Output source current	V _{E/AOut} = 4 V	-0.5	-1.3		mA
Output high voltage	$I_{E/AOut} = -0.5 \text{ mA}$	4.0	4.7	5.0	V
Output low voltage	I _{E/AOut} = 1 mA	0	0.5	1.0	V
Gain bandwidth product ⁽¹⁾	f = 200 kHz	5	10.5		MHz
Slew rate ⁽¹⁾		4	9		V/µs
PWM COMPARATOR					
Ramp bias current	$V_{Ramp} = 0 V$		-1	- 5	μΑ
Duty cycle range		0%		80%	
E/A out zero dc threshold	V _{Ramp} = 0 V	1.1	1.25		V
Delay to output ⁽¹⁾			50	80	ns
SOFT-START					
Charge current	V _{Soft Start} = 0.5 V	3	9	20	μΑ
Discharge current	V _{Soft Start} = 1 V	1			mA
CURRENT LIMIT/SHUTDOWN					
Current limit/shutdown bias current	0 < V _{ILIM/SD} < 4 V			15	μΑ
Current limit threshold		0.9	1.0	1.1	V
Shutdown threshold		1.25	1.40	1.55	V
Delay to output ⁽¹⁾			50	80	ns

⁽¹⁾ Parameters ensured by design and/or characterization, if not production tested.



ELECTRICAL CHARACTERISTICS (continued)

Unless otherwise stated, these specifications apply for $R_T = 3.65 \text{ k}\Omega$, $C_T = 1 \text{ nF}$, $V_{CC} = 15 \text{ V}$, $-55^{\circ}\text{C} < T_A < 125^{\circ}\text{C}$, $T_A = T_J$

PARAMETERS	TEST CONDITIONS	MIN	TYP	MAX	UNIT	
OUTPUT						
Low-level output voltage	I _{OUT} = 20 mA		0.25	0.40	V	
ow-level output voltage	I _{OUT} = 200 mA		1.2	2.2	V	
I Each Lovel autout valtage	I _{OUT} = -20 mA	13.0	13.5		V	
High-level output voltage	$I_{OUT} = -200 \text{ mA}$	12.0	13.0		V	
Collector leakage	V _C = 30 V		10	500	μΑ	
Rise/fall time (2)	C _L = 1 nF		30	75	ns	
UNDER-VOLTAGE LOCKOUT						
Start threshold		8.8	9.2	9.6	V	
UVLO hysteresis		0.4	0.8	1.2	V	
SUPPLY CURRENT SECTION						
Startup current	V _{CC} = 8 V		1.1	2.5	mA	
I _{cc}	$V_{INV} = V_{Ramp} = V_{ILIM/SD} = 0 \text{ V}, V_{NI} = 1 \text{ V}$		22	33	mA	

⁽²⁾ Parameters ensured by design and/or characterization, if not production tested.



PRINTED CIRCUIT BOARD LAYOUT CONSIDERATIONS

High speed circuits demand careful attention to layout and component placement. To ensure proper performance of the UC1825 follow these rules:

- 1. Use a ground plane.
- 2. Damp or clamp parasitic inductive kick energy from the gate of driven MOSFETs. Do not allow the output pins to ring below ground. A series gate resistor or a shunt 1-A Schottky diode at the output pin serves this purpose.
- 3. Bypass V_{CC}, V_C, and V_{REF}. Use 0.1-µF monolithic ceramic capacitors with low equivalent series inductance. Allow less than 1-cm of total lead length for each capacitor between the bypassed pin and the ground plane.
- 4. Treat the timing capacitor, C_T, like a bypass capacitor.

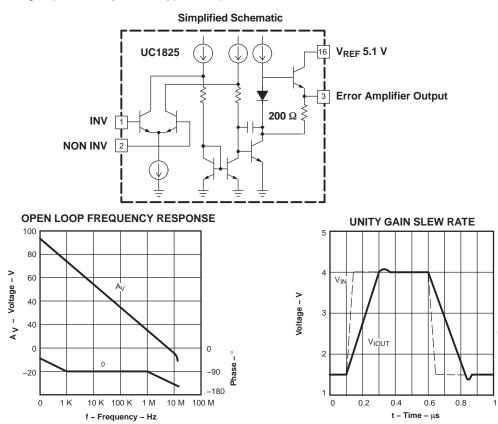


Figure 2. Error Amplifier



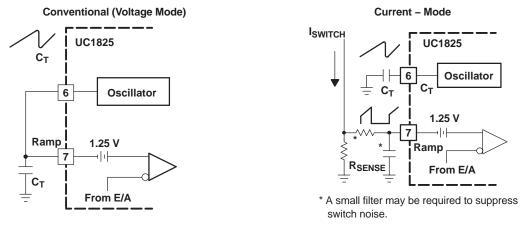


Figure 3. PWM Applications

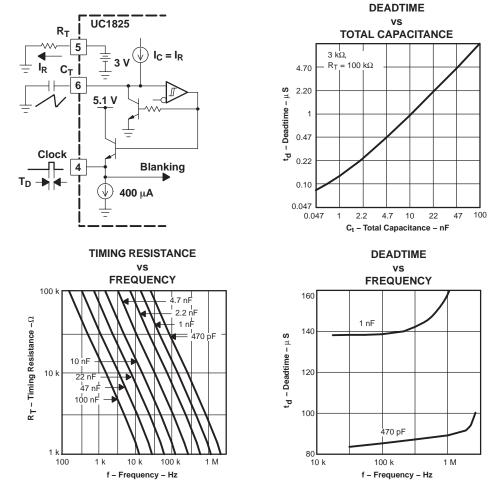


Figure 4. Oscillator Circuit



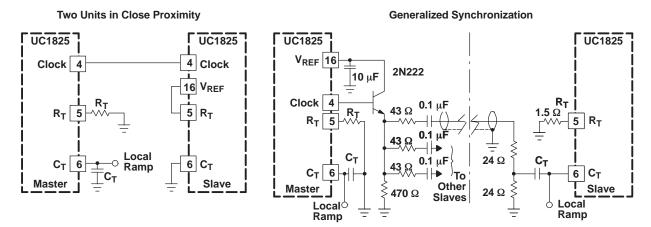


Figure 5. Synchronized Operation

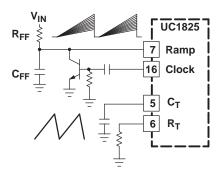


Figure 6. Forward Technique for Off-Line Voltage Mode Application

The circuit shown in Figure 6 will achieve a constant volt-second product clamp over varying input voltages. The ramp generator components, R_T and C_R are chosen so that the ramp at the ILIM/SD pin crosses the 1-V threshold at the same time the desired maximum volt-second product is reached. The delay through the functional nor block must be such that the ramp capacitor can be completely discharged during the minimum deadtime.

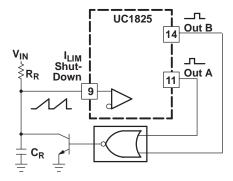


Figure 7. Constant Volt-Second Clamp Circuit



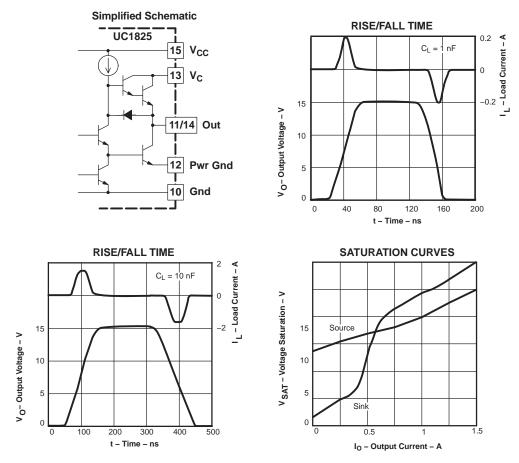


Figure 8. Output Section

The circuit in Figure 8 is useful for exercising many of the UC1825 functions and measuring their specifications.

As with any wideband circuit, careful grounding and bypass procedures should be followed. The use of a ground plane is highly recommended.



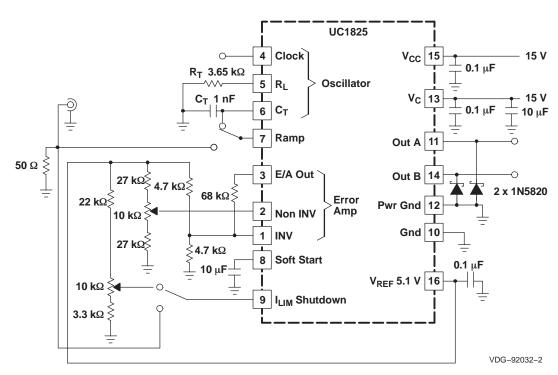


Figure 9. Open-Loop Laboratory Test Fixture



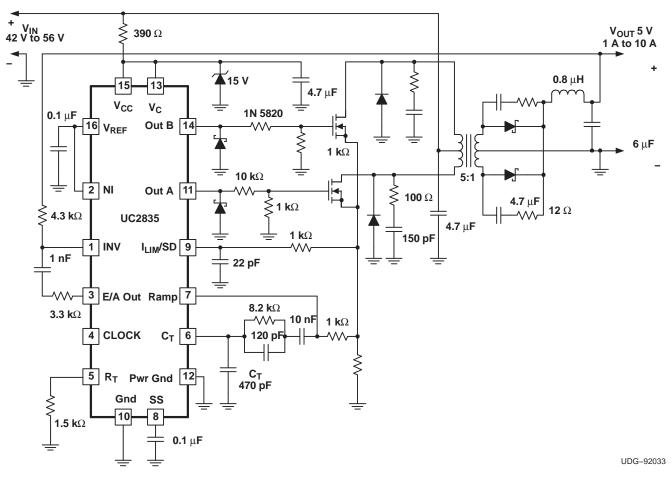


Figure 10. Design Example: 50 W, 48-V to 5-V DC-to-DC Converter – 1.5-MHz Clock Frequency





REVISION HISTORY

Cł	nanges from Original (January, 2009) to Revision A	Page
•	Added MAX spec of 16% to temperature stability parameter	5

www.ti.com 10-Jun-2022

PACKAGING INFORMATION

Orderable Device	Status (1)	Package Type	Package Drawing		Package Qty	Eco Plan	Lead finish/ Ball material	MSL Peak Temp	Op Temp (°C)	Device Marking (4/5)	Samples
5962-8768101V2A	ACTIVE	LCCC	FK	20	1	Non-RoHS & Green	SNPB	N / A for Pkg Type	-55 to 125	5962- 8768101V2A UC1825L QMLV	Samples
5962-8768101VEA	ACTIVE	CDIP	J	16	1	Non-RoHS & Green	SNPB	N / A for Pkg Type	-55 to 125	5962-8768101VE A UC1825JQMLV	Samples
5962-8768104V2A	ACTIVE	LCCC	FK	20	1	Non-RoHS & Green	SNPB	N / A for Pkg Type	-55 to 125	5962- 8768104V2A UC1825FK -SP	Samples
5962-8768104VEA	ACTIVE	CDIP	J	16	1	Non-RoHS & Green	SNPB	N / A for Pkg Type	-55 to 125	5962-8768104VE A UC1825J-SP	Samples

⁽¹⁾ The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

OBSOLETE: TI has discontinued the production of the device.

(2) RoHS: TI defines "RoHS" to mean semiconductor products that are compliant with the current EU RoHS requirements for all 10 RoHS substances, including the requirement that RoHS substance do not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, "RoHS" products are suitable for use in specified lead-free processes. TI may reference these types of products as "Pb-Free".

RoHS Exempt: TI defines "RoHS Exempt" to mean products that contain lead but are compliant with EU RoHS pursuant to a specific EU RoHS exemption.

Green: TI defines "Green" to mean the content of Chlorine (CI) and Bromine (Br) based flame retardants meet JS709B low halogen requirements of <=1000ppm threshold. Antimony trioxide based flame retardants must also meet the <=1000ppm threshold requirement.

- (3) MSL, Peak Temp. The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.
- (4) There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.
- (5) Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.

PACKAGE OPTION ADDENDUM

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(6) Lead finish/Ball material - Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

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OTHER QUALIFIED VERSIONS OF UC1825-SP:

Catalog: UC1825

NOTE: Qualified Version Definitions:

Catalog - TI's standard catalog product

PACKAGE MATERIALS INFORMATION

www.ti.com 5-Jan-2022

TUBE



*All dimensions are nominal

Device	Package Name	Package Type	Pins	SPQ	L (mm)	W (mm)	T (µm)	B (mm)
5962-8768101V2A	FK	LCCC	20	1	506.98	12.06	2030	NA
5962-8768104V2A	FK	LCCC	20	1	506.98	12.06	2030	NA

8.89 x 8.89, 1.27 mm pitch

LEADLESS CERAMIC CHIP CARRIER

This image is a representation of the package family, actual package may vary. Refer to the product data sheet for package details.



14 LEADS SHOWN



NOTES:

- A. All linear dimensions are in inches (millimeters).
- B. This drawing is subject to change without notice.
- C. This package is hermetically sealed with a ceramic lid using glass frit.
- D. Index point is provided on cap for terminal identification only on press ceramic glass frit seal only.
- E. Falls within MIL STD 1835 GDIP1-T14, GDIP1-T16, GDIP1-T18 and GDIP1-T20.

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